Dual Matched General Purpose Transistor

PNP Matched Pair

These transistors are housed in an ultra-small SOT-363 package ideally suited for portable products. They are assembled to create a pair of devices highly matched in all parameters, eliminating the need for costly trimming. Applications are Current Mirrors; Differential, Sense and Balanced Amplifiers; Mixers; Detectors and Limiters. Complementary NPN equivalent NST45011MW6T1G is available.

Features

- Current Gain Matching to 10%
- Base–Emitter Voltage Matched to ≤ 2 mV
- Drop-In Replacement for Standard Device
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-45	V
Collector - Base Voltage	V_{CBO}	-50	V
Emitter – Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I _C	-100	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

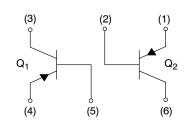
Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) T _A = 25°C	P _D	380 250	mW
Derate Above 25°C		3.0	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

^{1.} $FR-5 = 1.0 \times 0.75 \times 0.062$ in



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SOT-363 CASE 419B STYLE 1

MARKING DIAGRAMS



4F = Device Code M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]		
NST45010MW6T1G	SOT-363 (Pb-Free)			

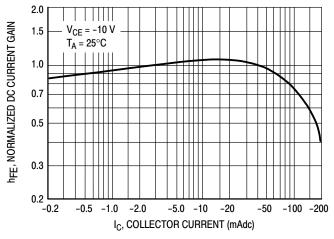
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage, (I _C = -10 mA)	V _{(BR)CEO}	-45	_	_	V
Collector – Emitter Breakdown Voltage, (I _C = –10 μA, V _{EB} = 0)	V _{(BR)CES}	-50	_	-	V
Collector – Base Breakdown Voltage, (I _C = –10 μA)	V _{(BR)CBO}	-50	_	-	V
Emitter – Base Breakdown Voltage, (I _E = -1.0 μA)	V _{(BR)EBO}	-5.0	_	-	V
Collector Cutoff Current ($V_{CB} = -30 \text{ V}$) ($V_{CB} = -30 \text{ V}$, $T_A = 150^{\circ}\text{C}$)	I _{CBO}	-	- -	-15 -5.0	nA μA
ON CHARACTERISTICS			-		
DC Current Gain $ \begin{array}{l} (I_C = -10~\mu A,~V_{CE} = -5.0~V) \\ (I_C = -2.0~m A,~V_{CE} = -5.0~V) \\ (I_C = -2.0~m A,~V_{CE} = -5.0~V)~(Note~2) \end{array} $	h _{FE}	- 220 0.9	150 290 1.0	- 475 -	-
Collector – Emitter Saturation Voltage ($I_C = -10$ mA, $I_B = -0.5$ mA) ($I_C = -100$ mA, $I_B = -5.0$ mA)	V _{CE(sat)}	- -	- -	-300 -650	mV
Base – Emitter Saturation Voltage (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{BE(sat)}	-	-700 -900	- -	mV
Base – Emitter On Voltage $ \begin{array}{l} (I_C = -2.0 \text{ mA, V}_{CE} = -5.0 \text{ V}) \\ (I_C = -10 \text{ mA, V}_{CE} = -5.0 \text{ V}) \\ (I_C = -2.0 \text{ mA, V}_{CE} = -5.0 \text{ V}) \end{array} $ (Note 3)	$V_{BE(on)}$ $V_{BE(1)} - V_{BE(2)}$	-600 - -	- - -1.0	-750 -820 -2.0	mV
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product, (I _C = –10 mA, V _{CE} = –5 Vdc, f = 100 MHz)	f _T	100	_	-	MHz
Output Capacitance, (V _{CB} = -10 V, f = 1.0 MHz)	C _{ob}	-	_	4.5	pF
Noise Figure, (I _C = -0.2 mA, V _{CE} = -5 Vdc, R _S = 2 k Ω , f = 1 kHz, BW = 200Hz)	NF	1		10	dB

h_{FE(1)}/h_{FE(2)} is the ratio of one transistor compared to the other transistor within the same package. The smaller h_{FE} is used as numerator.
 V_{BE(1)} - V_{BE(2)} is the absolute difference of one transistor compared to the other transistor within the same package.

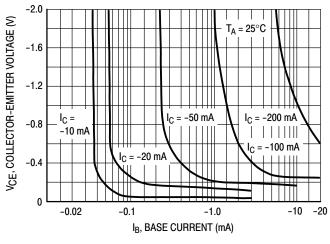
TYPICAL CHARACTERISTICS



 $T_A = 25^{\circ}C$ -0.9 $V_{BE(sat)} @ I_C/I_B = 10$ -0.8 V, VOLTAGE (VOLTS) -0.7 $V_{BE(on)} @ V_{CE} = -10 V$ -0.6 -0.5 -0.4 -0.3 -0.2 $V_{CE(sat)} @ I_C/I_B = 10$ -0.1 -0.1 -0.2 -1.0 -2.0 -5.0 -10 -50 -100 IC, COLLECTOR CURRENT (mAdc)

Figure 1. Normalized DC Current Gain

Figure 2. "Saturation" and "On" Voltages



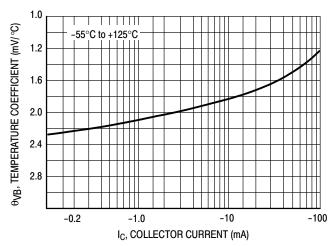
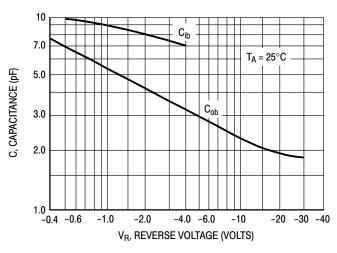


Figure 3. Collector Saturation Region

Figure 4. Base-Emitter Temperature Coefficient



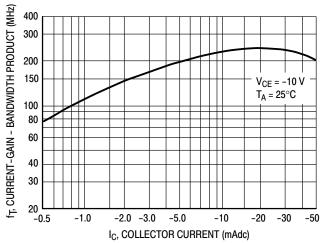


Figure 5. Capacitances

Figure 6. Current-Gain - Bandwidth Product

TYPICAL CHARACTERISTICS

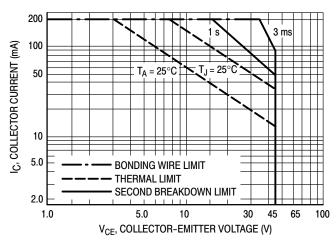


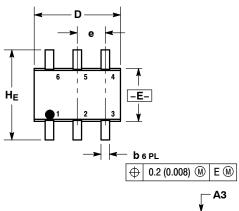
Figure 7. Active Region Safe Operating Area

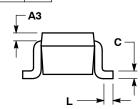
The safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 7 is based upon $T_{J(pk)}$ = 150°C; T_{C} or T_{A} is variable depending upon conditions.

PACKAGE DIMENSIONS

SC-88 (SOT-363) CASE 419B-02 ISSUF W





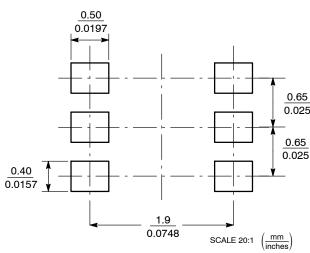
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
А3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
С	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

STYLE 1: PIN 1. EMITTER 2

- 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1
- BASE 1
- **COLLECTOR 2**

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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